2N3771, 2N3772

High Power NPN Silicon Power Transistors

These devices are designed for linear amplifiers, series pass regulators, and inductive switching applications.

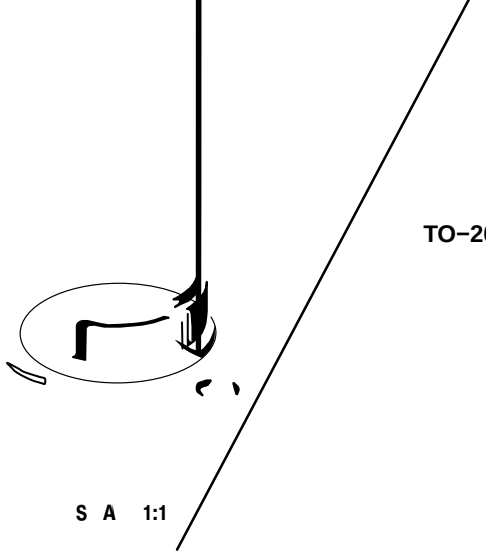
Features

- Forward Biased Second Breakdown Current Capability
  $I_{S/b}$ = 3.75 Adc @ V_{CE} = 40 Vdc − 2N3771
  = 2.5 Adc @ V_{CE} = 60 Vdc − 2N3772
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	2N3771	2N3772	Unit
−				
−				
−				
−				

ELECTRICAL CHARACTERISTICS °



TO−204 (TO−3)

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